

2SK3984-ZK-E2-AZ-VB Datasheet N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
100	0.114 at V _{GS} = 10 V	15			

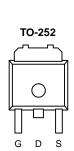
FEATURES

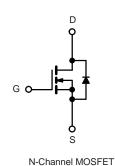
- Trench Power MOSFET
- 150 °C Junction Temperature
- PWM Optimized
- 100 % R_a Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

· Primary Side Switch





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	100	V		
Gate-Source Voltage	V _{GS}	± 20				
Continuous Drain Current (T _{.I} = 175 °C) ^b	T _C = 25 °C	I _D	15			
Continuous Drain Current (1 _J = 175 °C)	T _C = 125 °C	l 'b	13			
Pulsed Drain Current	I _{DM}	40	A			
Continuous Source Current (Diode Conduction)	I _S	3				
Avalanche Current	I _{AS}	3				
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	18	mJ		
Maximum Dowar Dissination	T _C = 25 °C	P _D	96 ^b	W		
Maximum Power Dissipation	T _A = 25 °C	' 0	3 ^a] vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
hungation to Ambiens	t ≤ 10 s	R _{thJA}	15	18	°C/W		
Junction-to-Ambient ^a	Steady State		40	50			
Junction-to-Case (Drain)	•	R _{thJC}	0.85	1.1			

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 100 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		0.114		0	
Drain Causes On Chata Desistance	R	V _{GS} = 10 V, I _D = 3 A, T _J = 125 °C		0.120			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 3 A, T _J = 175 °C		0.140		Ω	
		$V_{GS} = 4.5 \text{ V } I_D = 3 \text{ A}$	0.120			7	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 3 A		35		S	
Dynamic ^a							
Input Capacitance	C_{iss}			950		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, F = 1 \text{ MHz}$		120			
Reverse Transfer Capacitance	C _{rss}			60			
Total Gate Charge ^c	Q_g			24	41		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$		8		nC	
Gate-Drain Charge ^c	Q_{gd}			12			
Gate Resistance	R_g		0.5		2.9	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	25		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 5.2 \Omega$		50	75	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 3 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45	115	
Fall Time ^c	t _f			60	90		
Source-Drain Diode Ratings and Char	acteristics (7	T _C = 25 °C)					
Pulsed Current	I _{SM}				5	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 3 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3 A, dI/dt = 100 A/μs		180	250	ns	

Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

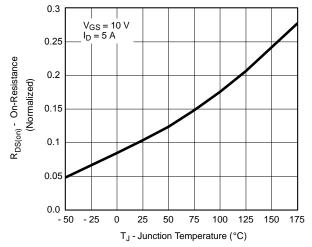


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

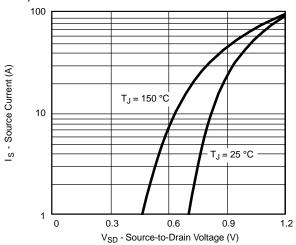




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

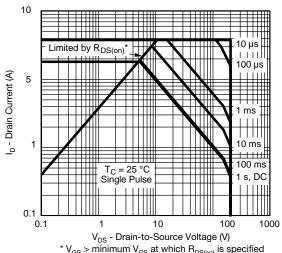


Source-Drain Diode Forward Voltage

THERMAL RATINGS

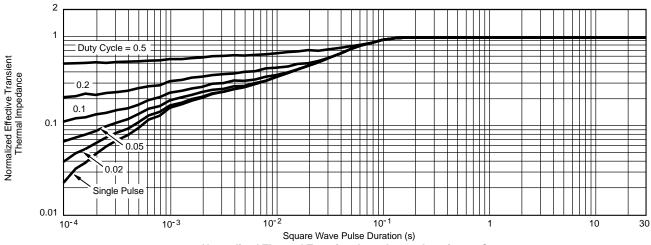


Maximum Avalanche Drain Current vs. Case Temperature



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

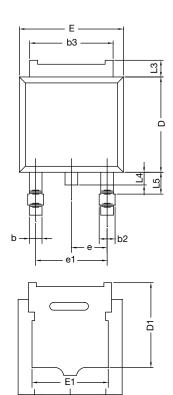
Safe Operating Area

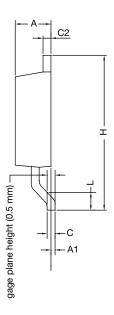


Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	2.28 BSC		BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

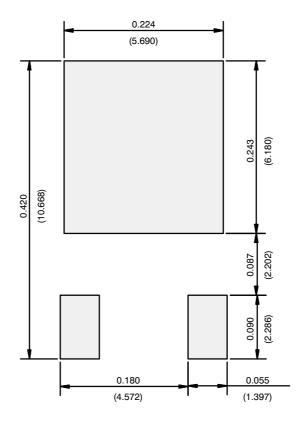
Note

• Dimension L3 is for reference only.

服务热线:400-655-8788



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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